Experiment No. 5 MEMORY DESIGN USING STATIC RANDOM ACCESS MEMORY (RAM) ECE 441

Peter Chinetti

October 30, 2013

Date Performed:	October 10,17, & 24, 2013
Partners:	Zelin Wu
Instructor:	Professor Saniie

1 Introduction

1.1 Purpose

The purpose of this experiment is to familiarize the user with the following devices and concepts:

- Static Random Access Memory (SRAM)
- Open Collector Devices
- the SANPER-1 ELUS Block Select Lines

1.2 Background

1.3 MC68000 Asynchronous Bus Interface

The MC68000 has a 16-bit data bus, and byte accesses of memory locations are permitted from either an even or an odd address.

1.4 Open Collector Devices

A standard TTL type device has two output transistors that form the output driver for the logic gate. One transistor sits about the other one. That is, the emitter of the top transistor is tied to the collector of the bottom transistor. The top transistor function acts as an active pullup for the bottom transistor. For example, a 74LS04 logic device consists of six inverters. Each inverter consists of two transistors that form the output driver. One of the transistors is used as an active pullup for the other transistor. On the other hand, a TTL logic device with open collector outputs has only one transistor acting as the output driver. The collector of the transistor is left floating or open. Hence the name open collector output. The IC manufacturer expects the design engineer to add whatever external pullup mechanism he/she deems appropriate for the circuit to function properly.

Since a standard TTL type logic gate has a pullup mechanism built in, these outputs cannot be tied together due to possible contention problems. For example, if one of the device is trying to drive its output low, while another device is trying to drive its output high, one of the two devices will win the contention battle, while the other device will have its output transistor destroyed.

On the other hand, since devices with open collector outputs do not have a built in pullup mechanism, several open collector outputs can be tied together without damaging any of the output drivers. When all the outputs are tied together, it forms a single bus line. A resistor can then be used as an external pullup mechanism for this bus line.

A good application for devices with open collector outputs is found in microprocessor systems. If several peripheral devices exist in the system, the Interrupt Request Lines (*IRQ) or each of these devices can be connected together and then connected to the *IRQ input of the microprocessor. A resistor is connected between this *IRQ bus line and the logic supply voltage (typically +5V DC). Thus one of the peripheral devices can assert the *IRQ line without damaging the other devices. Note this technique can only be employed if the device is equipped with an open collector output on its *IRQ line.

1.5 The SANPER-1 ELU'S Block Select Lines

There are four Block Select lines (*Q5, *Q6, *Q7, *Q8) provided on the System Expansion Board which can be used for decoding and selecting external devices. Each of the Block Select lines was obtained by decoding address A16 through A23 and Address Strobe (*AS). Thus one of these Block Select lines can be used as an input to any additional external address decoding circuitry.

The SANPER-1 ELU Memory Map indicates the address ranges associated with each of the Block Select lines.

2 Lab Procedure and Equipment List

2.1 Equipment

- SANPER System
- Computer with TUTOR software

2.2 Procedure

Design and implement memory, then test with a memory test program.

3 Results, Analysis and Discussion

3.1 Memory Test Program

	ORC	G \$900	
MSGPAS	DC.B	'MEMORY TEST PA	SSED'
MSGENP	DS.B	1	
START:	ORG \$10		
	MOVE. L		
	MOVE. L	11 /	
LOOP:	MOVE. B		; Write out 0xAA to memory
		CMPA . L A5, A6	
	BNE	LOOP	;Loop back
	MOVE. L	11 /	;Go back to start
CHECK_AA:	CM₽.B	$\#\!\!\!\mathrm{SAA},(\mathrm{A5})$; Make sure AA got written out
	BNE	FAIL_AA	; If it didn't fail
	MOVE. B		; $Write 0x55 out$
	CM₽. L	A5, A6	; until done with range
	BNE	CHECK_AA	;loop back
	MOVE. L		;Go back to start
CHECK_55:	CM₽.B	#\$55, (A5)	; Check 0x55 can be read
	BNE	FAIL_55	; fail
	MOVE.B		; write AA out
	CMPA. L	A5, A6	; until done with range
	BNE	CHECK_55	; loop
	LEA	MSGPAS, A5	;load string addr into A5
	LEA	MSGENP, A6	; load A6
	JMP	OUTPUT	; jump to success
FAIL_AA:		#\$2000,A6	;load A6
	MOVE. L	·	
	MOVE. B	#231,D7	;PNT6HX
	TRAP	#14	
	MOVE. B		; space
	MOVE. B		;A
	MOVE. B		;A
	MOVE. B		; space
		(A5), D0	. DNT0HY
	MOVE. B	#233,D7	;PNT2HX
	TRAP MOVE. L	$\#14 \\ \#\$2000, A5$	east start of output
	JMP	#52000, A5 OUTPUT	; set start of output ; jump to output w/ string 'AA'
	JIVII-	001101	, jump to output w/ string AA

FAIL_55:	MOVE. L	#\$2000, A6	
	MOVE. L	A5, D0	
	MOVE. B	#231,D7	;PNT6HX
	TRAP	#14	
	MOVE.B	#\$20,(A6)+	; space
	MOVE.B	#\$35,(A6)+	; 5
	MOVE.B	#\$35,(A6)+	; 5
	MOVE.B	#\$20,(A6)+	; space
	MOVE.B	(A5), D0	
	MOVE.B	#233, D7	
	TRAP	#14	
	MOVE. L	#\$2000, A5	; set $start$
OUTPUT:	MOVE.B	#243, D7	; $OUTPUT$
	TRAP	#14	
	MOVE.B	#228, D7	; TUTOR
	TRAP	#14	
	END STA	RT	



3.2 Diagram

3.3 Memory Location

Memory was placed at the 082000 address, because it had a simple address to decode.

3.4 Memory Test Design

The memory test program tests that 0xAA (10101010b) can be written and read, then that 0x55 (01010101b) can be written and read. Another useful pattern to write would be 0x00FF and 0xFF00 so upper and lower byte order can be checked.

3.5 Why SRAM

SRAM is easy to use, as it does not require refreshes like DRAM does, and the high density possible with DRAM is not required for a 1K block.

4 Conclusions

This experiment was accomplished. A memory bank was built and tested.